N-channel 40 V, 3.3 mΩ standard level MOSFET in LFPAK33
29 January 2019 Product data sheet

## 1. General description

Automotive qualified standard level N-channel MOSFET in an LFPAK33 package using Trench 9 TrenchMOS technology. This product has been designed and qualified to AEC-Q101 for use in high performance automotive applications.

### 2. Features and benefits

- Fully automotive qualified to AEC-Q101 at 175 °C
- Trench 9 superjunction technology:
  - · Low power losses, high power density
- LFPAK copper clip package technology:
  - · High robustness and reliability
  - · Gull wing leads for high manufacturability and AOI
- Repetitive avalanche rated

## 3. Applications

- · 12 V automotive systems
- · Powertrain, chassis, body and infotainment applications
- · Medium/Low power motor drive
- · DC-DC systems
- · LED lighting

### 4. Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C		-	-	40	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>	[1]	-	-	80	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>		-	-	101	W
Static characte	eristics						
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 ^{\circ}\text{C};$ Fig. 11		1.8	2.6	3.3	mΩ
Dynamic chara	ecteristics		•				
$Q_{GD}$	gate-drain charge	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 32 V; V <sub>GS</sub> = 10 V; Fig. 13; Fig. 14		-	6.6	13.2	nC
Source-drain d	liode		•				
Q <sub>r</sub>	recovered charge	$I_S = 25 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V}; V_{DS} = 20 \text{ V}; Fig. 17$		-	21	-	nC



Symbol	Parameter	Conditions	Min	Тур	Max	Unit
S		$I_S = 25 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V}; V_{DS} = 20 \text{ V}; T_j = 25 ^{\circ}\text{C}; Fig. 16$	-	0.68	-	

<sup>[1] 80</sup>A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.

## 5. Pinning information

### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline		Graphic symbol
1	S	source		7	D
2	S	source			
3	S	source			G—(F)
4	G	gate			mbb076 S
mb	D	Mounting base; connected to drain	1 2 3 4 LFPAK33 (SOT1)	<b></b> 210)	

# 6. Ordering information

### **Table 3. Ordering information**

Type number	mber Package				
	Name	Description	Version		
BUK7M3R3-40H	LFPAK33	Plastic, single ended surface mounted package (LFPAK33); 8 leads; 0.65 mm pitch	SOT1210		

# 7. Marking

## Table 4. Marking codes

Type number	Marking code
BUK7M3R3-40H	73H340

# 8. Limiting values

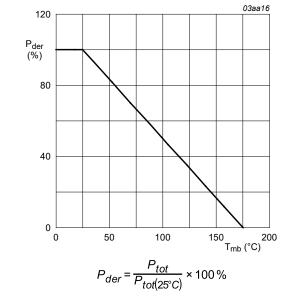
#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

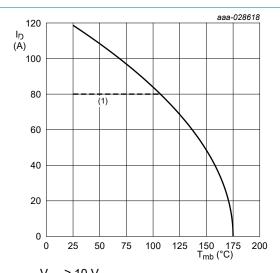
Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C		-	40	V
$V_{GS}$	gate-source voltage	DC; T <sub>j</sub> ≤ 175 °C		-10	20	V
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>		-	101	W
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>	[1]	-	80	А
		V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 100 °C; <u>Fig. 2</u>		-	80	Α
I <sub>DM</sub>	peak drain current	pulsed; $t_p \le 10 \mu s$ ; $T_{mb} = 25 °C$ ; Fig. 3		-	475	А
T <sub>stg</sub>	storage temperature			-55	175	°C
T <sub>j</sub>	junction temperature			-55	175	°C
Source-drai	n diode					

Symbol	Parameter	Conditions		Min	Max	Unit	
Is	source current	T <sub>mb</sub> = 25 °C		-	80	А	
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \mu s$ ; $T_{mb} = 25 °C$		-	475	Α	
Avalanche rug	Avalanche ruggedness						
E <sub>DS(AL)S</sub>	non-repetitive drain- source avalanche energy	$I_D$ = 80 A; $V_{sup} \le 40$ V; $R_{GS}$ = 50 Ω; $V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; unclamped; Fig. 4	[2] [3]	-	57	mJ	

- 80A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.
- Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.
- Refer to application note AN10273 for further information.



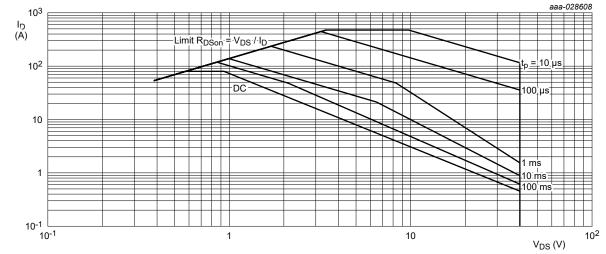
Normalized total power dissipation as a function of mounting base temperature



 $V_{GS} \ge 10 \text{ V}$ 

(1) 80A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.

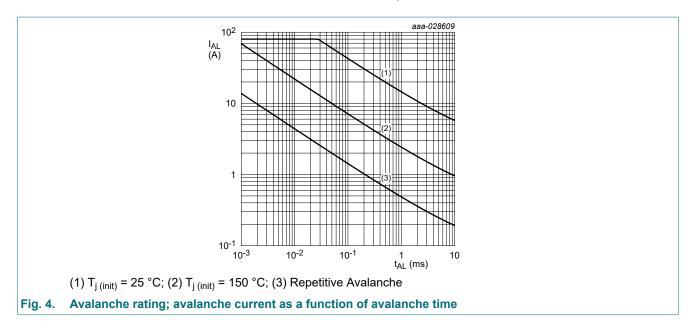
Fig. 2. Continuous drain current as a function of mounting base temperature



T<sub>mb</sub> = 25 °C; I<sub>DM</sub> is a single pulse

Safe operating area; continuous and peak drain currents as a function of drain-source voltage Fig. 3.

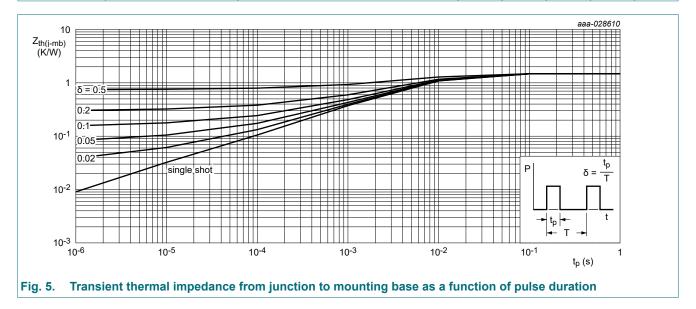
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### 9. Thermal characteristics

**Table 6. Thermal characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	<u>Fig. 5</u>	-	1.3	1.48	K/W



## 10. Characteristics

**Table 7. Characteristics** 

	140101101100						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static chara	cteristics		·				
V <sub>(BR)DSS</sub>	drain-source	I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C		40	43	-	V
(=: -)= = =	breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -40 ^{\circ} C$		-	40.5	-	V

BUK7M3R3-40H

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$	36	40	-	٧
V <sub>GS(th)</sub>	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS}=V_{GS}; T_j = 25 \text{ °C}; Fig. 9;$ Fig. 10	2.4	3	3.6	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C}; Fig. 9$	-	-	4.3	V
		I <sub>D</sub> = 1 mA; V <sub>DS</sub> =V <sub>GS</sub> ; T <sub>j</sub> = 175 °C; <u>Fig. 9</u>	1	-	-	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = 40 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.07	1	μΑ
		V <sub>DS</sub> = 16 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 125 °C	-	0.94	10	μΑ
		V <sub>DS</sub> = 40 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 175 °C	36   40   -	500	μΑ	
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	2	100	nA
		V <sub>GS</sub> = -10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	2	100	nA
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS}$ = 10 V; $I_D$ = 25 A; $T_j$ = 25 °C; Fig. 11	1.8	2.6	3.3	mΩ
		$V_{GS}$ = 10 V; $I_D$ = 25 A; $T_j$ = 105 °C; Fig. 12	2.5	4	5.3	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 125 °C; Fig. 12	2.8	4.4	5.8	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 175 °C; Fig. 12	3.5	5.5	7.2	mΩ
R <sub>G</sub>	gate resistance	f = 1 MHz; T <sub>j</sub> = 25 °C	0.3	0.8	2	Ω
Dynamic ch	naracteristics					
Q <sub>G(tot)</sub>	total gate charge	= 1 MHz; 1 <sub>j</sub> = 25 °C 0 = 25 A; V <sub>DS</sub> = 32 V; V <sub>GS</sub> = 10 V; ig. 13; Fig. 14	-	32	45	nC
Q <sub>GS</sub>	gate-source charge		-	9	14	nC
Q <sub>GD</sub>	gate-drain charge		-	6.6	13.2	nC
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 25 V; V <sub>GS</sub> = 0 V; f = 1 MHz;	-	2169	3037	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; <u>Fig. 15</u>	-	592	829	pF
C <sub>rss</sub>	reverse transfer capacitance		-	113	250	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = 30 \text{ V}; R_L = 1.2 \Omega; V_{GS} = 10 \text{ V};$	-	8.4	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 5 \Omega$	-	7.3	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	19	-	ns
t <sub>f</sub>	fall time		-	9.1	-	ns
Source-dra	in diode			<u> </u>		
V <sub>SD</sub>	source-drain voltage	I <sub>S</sub> = 25 A; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C; <u>Fig. 16</u>	-	0.82	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_S$ = 25 A; $dI_S/dt$ = -100 A/µs; $V_{GS}$ = 0 V; $V_{DS}$ = 20 V	-	27	-	ns
Q <sub>r</sub>	recovered charge	$I_S$ = 25 A; $dI_S/dt$ = -100 A/ $\mu$ s; $V_{GS}$ = 0 V; $V_{DS}$ = 20 V; Fig. 17	-	21	-	nC
S	softness factor	$I_S$ = 25 A; $dI_S/dt$ = -100 A/ $\mu$ s; $V_{GS}$ = 0 V; $V_{DS}$ = 20 V; $T_j$ = 25 °C; Fig. 16	-	0.68	-	
		$I_S$ = 25 A; $dI_S/dt$ = -500 A/ $\mu$ s; $V_{GS}$ = 0 V; $V_{DS}$ = 20 V; $T_j$ = 25 °C; Fig. 16	-	0.49	-	

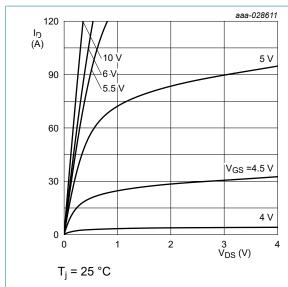


Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values

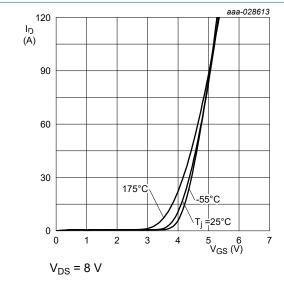


Fig. 8. Transfer characteristics; drain current as a function of gate-source voltage; typical values

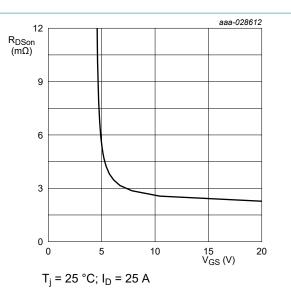


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

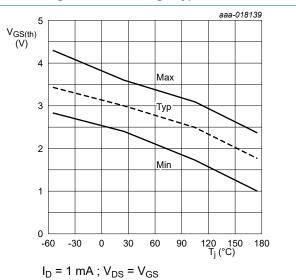


Fig. 9. Gate-source threshold voltage as a function of junction temperature

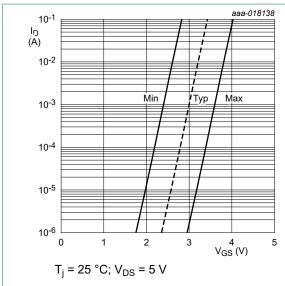


Fig. 10. Sub-threshold drain current as a function of gate-source voltage

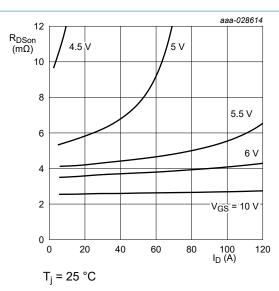


Fig. 11. Drain-source on-state resistance as a function of drain current; typical values

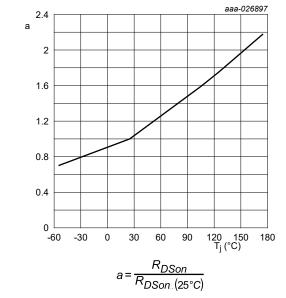


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

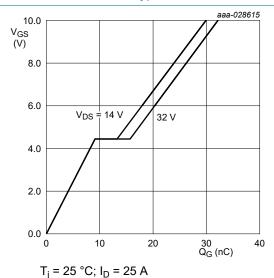


Fig. 13. Gate-source voltage as a function of gate charge; typical values

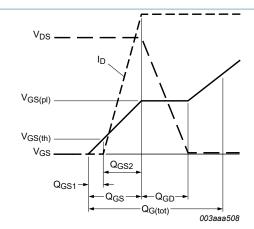
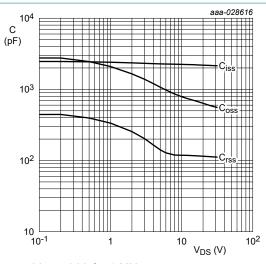


Fig. 14. Gate charge waveform definitions



 $V_{GS} = 0 V$ ; f = 1 MHz

Fig. 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

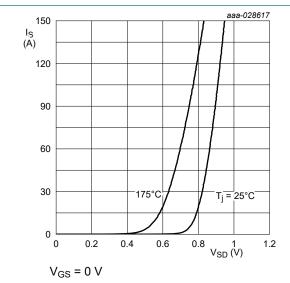


Fig. 16. Source-drain (diode forward) current as a function of source-drain (diode forward) voltage; typical values

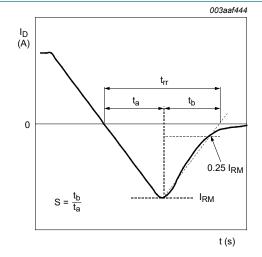
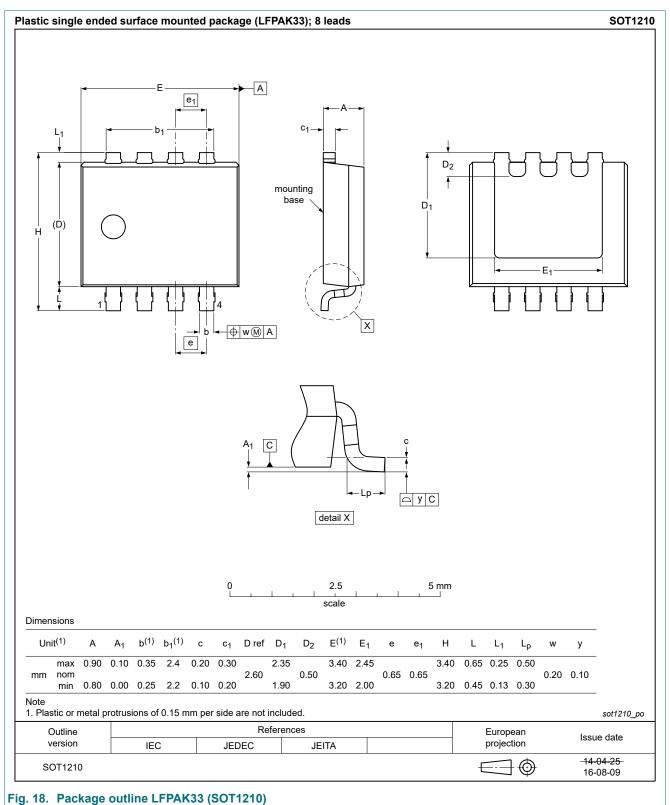


Fig. 17. Reverse recovery timing definition

# 11. Package outline



1 ig. 10. Tackage outline Li I Altos (001 1210)

## 12. Legal information

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Document status [1][2]	Product status [3]	Definition
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